



NS8002 2.4W Mono AB class audio power amplifier

1 Characteristic

- Output Power: 2.4W (RL=4Ω, THD=10%) Low leakage
- current in power-down mode: 1uA (typical)
- high level Shut-down
- use SOP8 encapsulation
- External gain adjustable
- voltage range 3.0V—5.25V
- No need to drive output coupling capacitors, bootstrap capacitors, and snubber networks
- Unity Gain Stable

2 Application range

- laptop
- Desktop PC
- Low voltage sound system

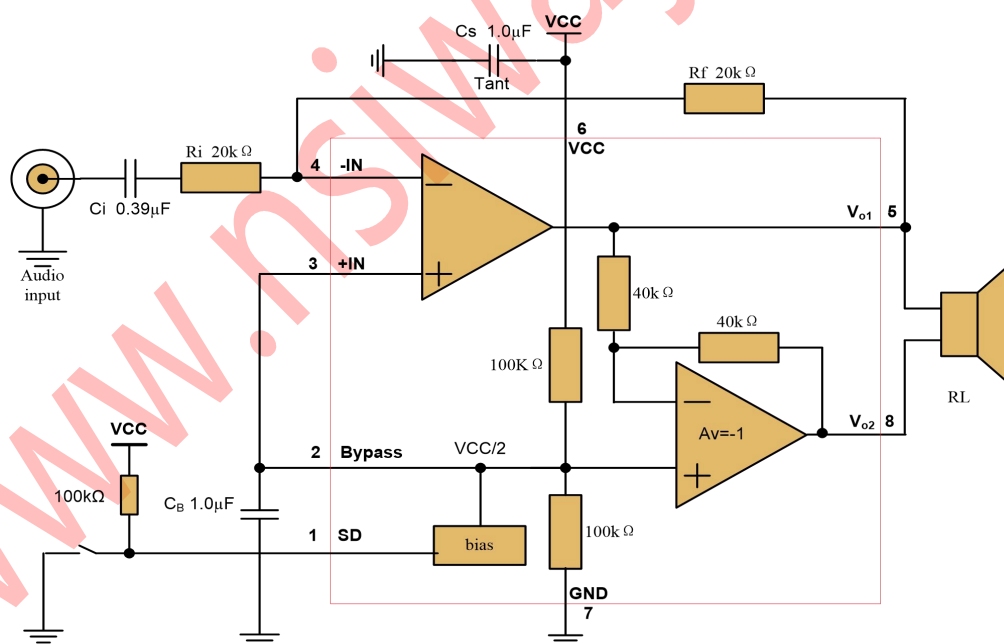
3 Illustrate

NS8002 is a AB Bridge-like output audio power amplifier. Its application circuit is simple and requires only a few peripheral devices. output not required External coupling capacitors or boost capacitors and buffer networks are required. SOP-8 package, more suitable for portable systems.

NS8002 Power consumption can be reduced by controlling entry into a low-power shutdown mode. Gain-bandwidth product up to 2.5MHz And unity gain stable. The voltage gain of the amplifier can be adjusted by configuring peripheral resistors, which is convenient for application.

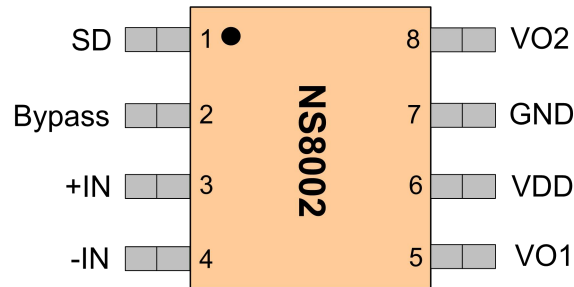
NS8002 supply SOP-8 package, rated for the operating temperature range of -40°C to 85°C.

4 Typical Application Circuit



5pin configuration

SOP-8The pinout diagram is shown in the figure below:



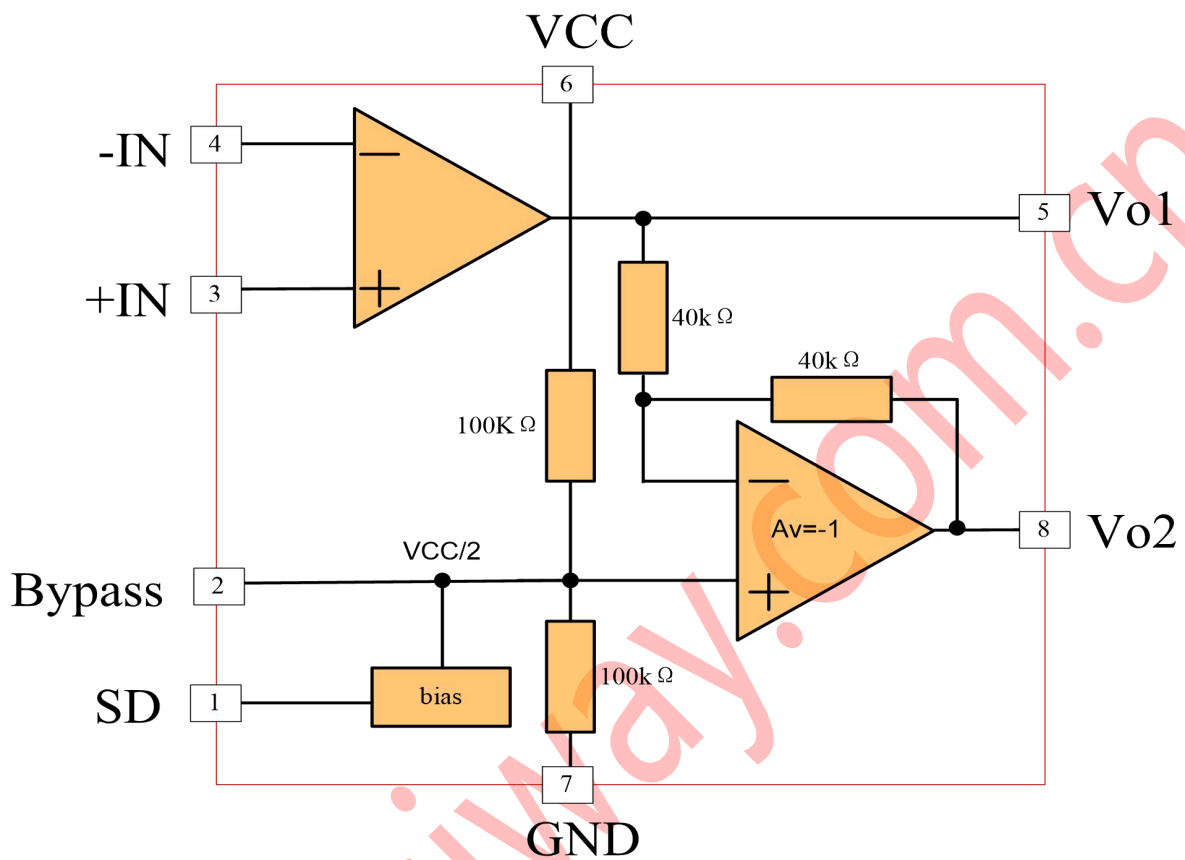
Numbering	Pin name	Pin Description
1	SD	Power-down control pin, high level off, low level on
2	Bypass	Internal Common Mode Voltage Bypass Capacitor
3	+ IN	Analog input, positive phase
4	- IN	Analog input, inverting
5	VO1	Analog output1
6	VDD	Power positive
7	GND	power ground
8	VO2	Analog output2

6Limit working parameters

- Power supply voltage range	2.8V ~ 5.5V
- Input voltage range	- 0.3V ~ VDDV
- ESDVoltage(HBM/MM)	3000V/250V
- range of working temperature	- 40°C ~ +85°C
- storage temperature range	-65°C ~ +150°C
- maximum junction temperature	+ 150°C
- soldering temperature (10sInside)	+ 220°C
- θ_{JC}/θ_{JA}	35/140°C/W

Note: Exceeding the above limit operating parameter range may cause permanent damage to the chip. Prolonged exposure to any of the above extreme conditions may affect chip reliability and lifetime.

7Structure diagram



Electrical characteristics

Working conditions (unless otherwise stated): $T=25^{\circ}\text{C}$, $V_{\text{DDB}}=5.0\text{V}$.

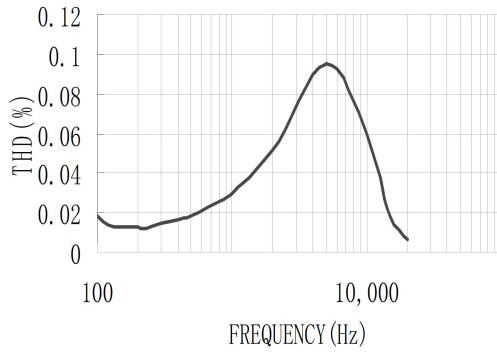
symbol	parameter	Test Conditions	minimum value	standard value	maximum value	unit
VDD	voltage		3.0		5.25	V
IDD	Power Quiescent Current	$V_{\text{IN}}=0\text{V}$, $I_{\text{O}}=0\text{A}$,		6	10	mA
ISD	OFF Leakage Current			1	20	μA
VOS	Output offset voltage			5.7	50	mV
RO	output resistance		7	8.5	10	K
PO	Output Power	THD=1%, $f=1\text{KHz}$ $R_{\text{L}}=4\Omega$ $R_{\text{L}}=8\Omega$		1.8 1.3		W
		THD+N=10%, $f=1\text{KHz}$ $R_{\text{L}}=4\Omega$ $R_{\text{L}}=8\Omega$		twenty four 1.7		W
THD+N	Total Distortion + Noise	AVD=2 $20\text{Hz}\leq f\leq 20\text{KHz}$ $R_{\text{L}}=4\Omega$, $P_{\text{O}}=1\text{W}$ $R_{\text{L}}=8\Omega$, $P_{\text{O}}=0.5\text{W}$		0.1 0.1		%
PSRR	Power Supply Rejection Ratio		65	80		dB
SNR	SNR	$R_{\text{L}}=4\Omega$, $P_{\text{O}}=1\text{W}$		85		dB

9 Typical characteristic curve

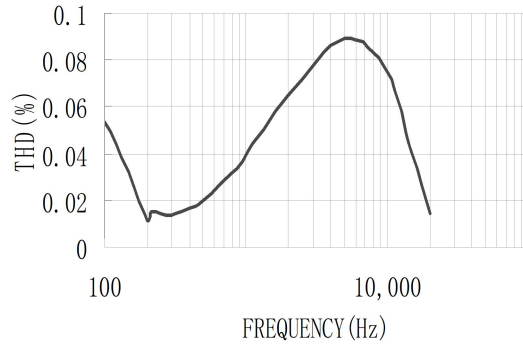
Of the following characteristic curves, unless conditions are specified, $T=25^{\circ}\text{C}$.

9.1 Total Harmonic Distortion (THD), distortion + noise (THD+N), SNR (S/N)

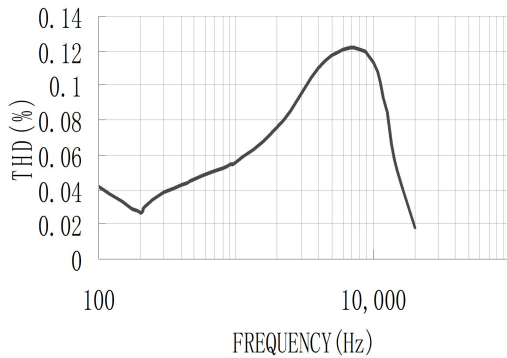
THD vs Frequency
 $T=25^{\circ}\text{C}$, $V_{dd}=5\text{V}$, $R_L=8\Omega$, and $P_o=500\text{mW}$



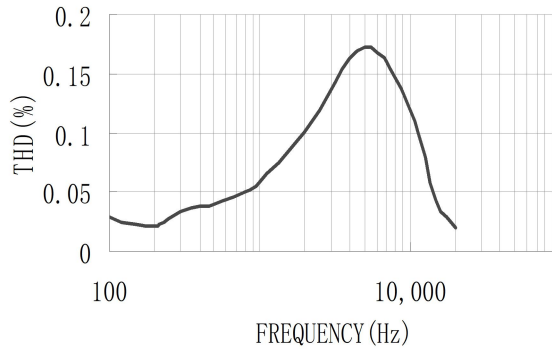
THD vs Frequency
 $T=25^{\circ}\text{C}$, $V_{dd}=3.3\text{V}$, $R_L=8\Omega$, and $P_o=425\text{mW}$



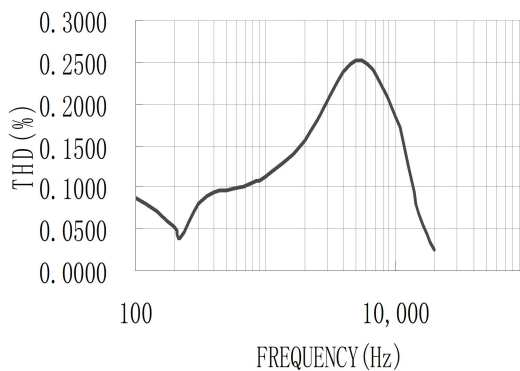
THD vs Frequency
 $T=25^{\circ}\text{C}$, $V_{dd}=2.5\text{V}$, $R_L=8\Omega$, and $P_o=150\text{mW}$



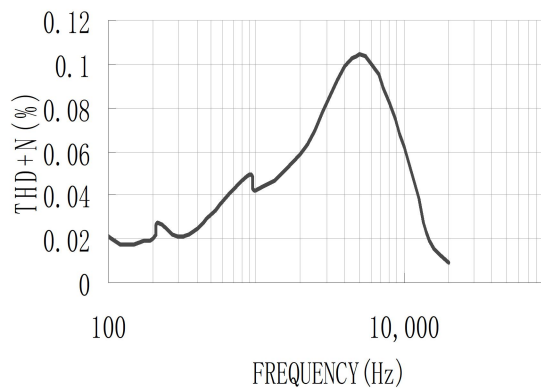
THD vs Frequency
 $T=25^{\circ}\text{C}$, $V_{dd}=3.3\text{V}$, $R_L=4\Omega$, and $P_o=425\text{mW}$



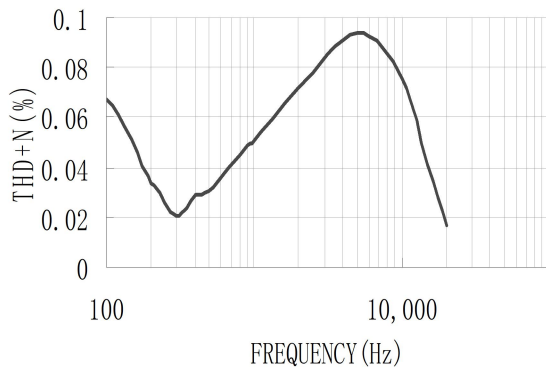
THD vs Frequency
 $T=25^{\circ}\text{C}$, $V_{dd}=2.5\text{V}$, $R_L=4\Omega$, and $P_o=150\text{mW}$



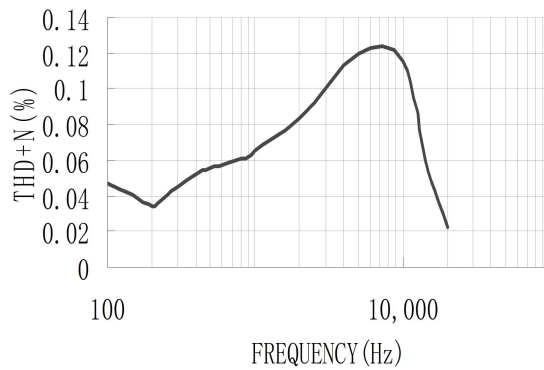
THD+N vs Frequency
 $T=25^{\circ}\text{C}$, $V_{dd}=5\text{V}$, $R_L=8\Omega$, and $P_o=500\text{mW}$



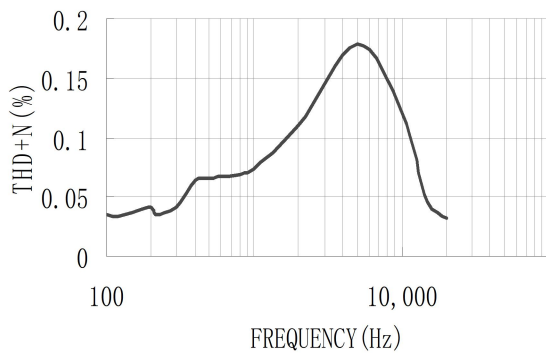
THD+N vs Frequency
T=25°C, Vdd=3.3V, RL=8Ω, and Po=425mW



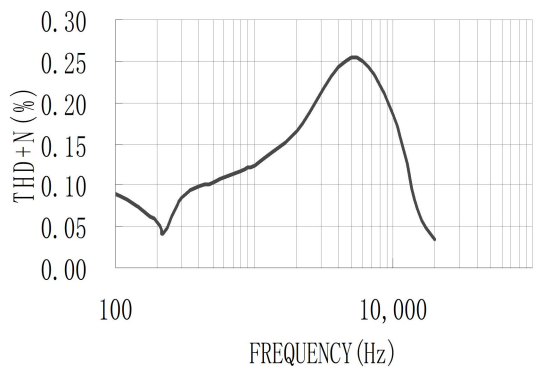
THD+N vs Frequency
T=25°C, Vdd=2.5V, RL=8Ω, and Po=150mW



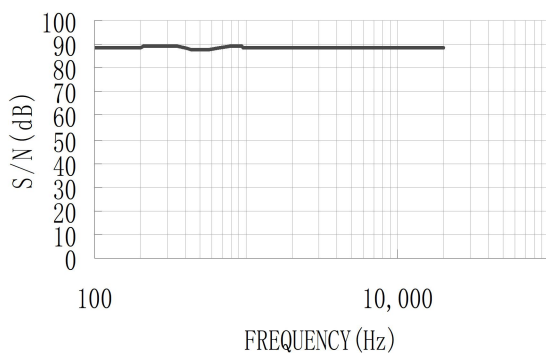
THD+N vs Frequency
T=25°C, Vdd=3.3V, RL=4Ω, and Po=425mW



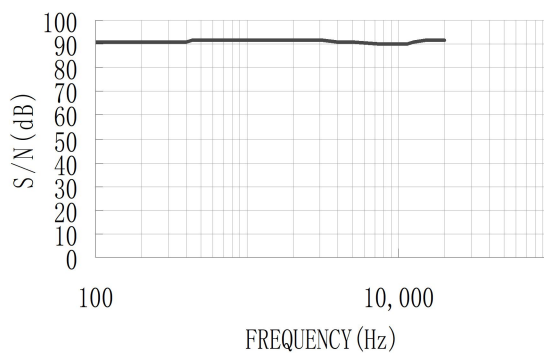
THD+N vs Frequency
T=25°C, Vdd=2.5V, RL=4Ω, and Po=150mW



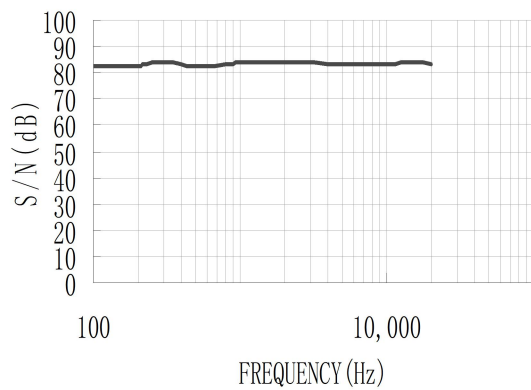
S/N vs Frequency
T=25°C, Vdd=5V, RL=8Ω, and Po=500mW



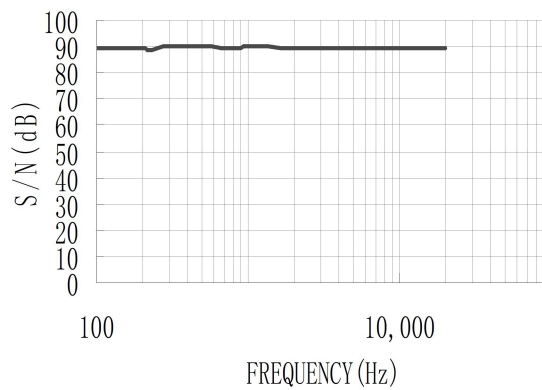
S/N vs Frequency
T=25°C, Vdd=3.3V, RL=8Ω, and Po=425mW



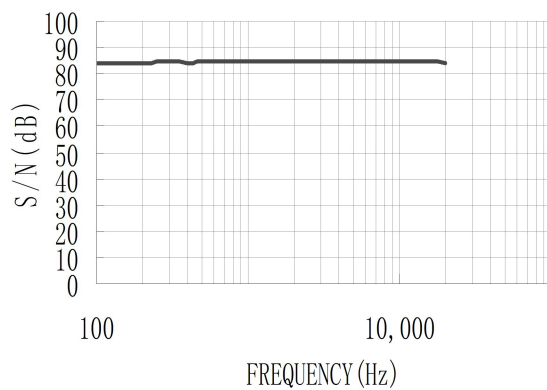
S/N vs Frequency
T=25°C, Vdd=2.5V, RL=8Ω, and Po=150mW



S/N vs Frequency
T=25°C, Vdd=3.3V, RL=4Ω, and Po=425mW

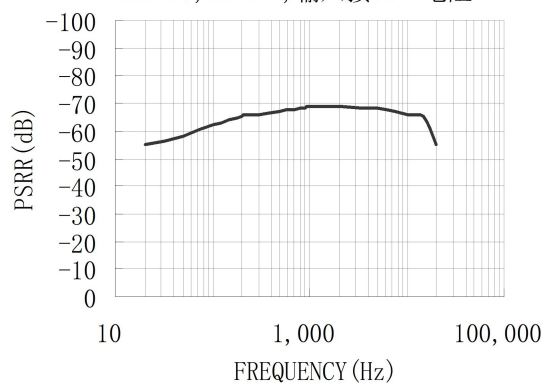


S/N vs Frequency
T=25°C, Vdd=2.5V, RL=4Ω, and Po=150mW

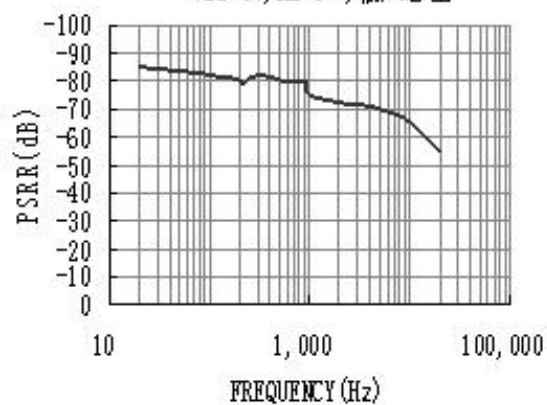


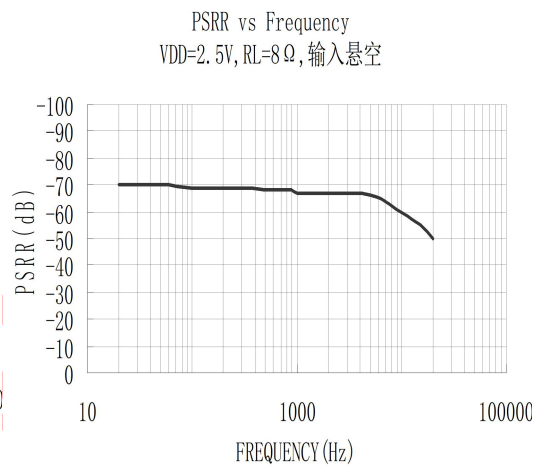
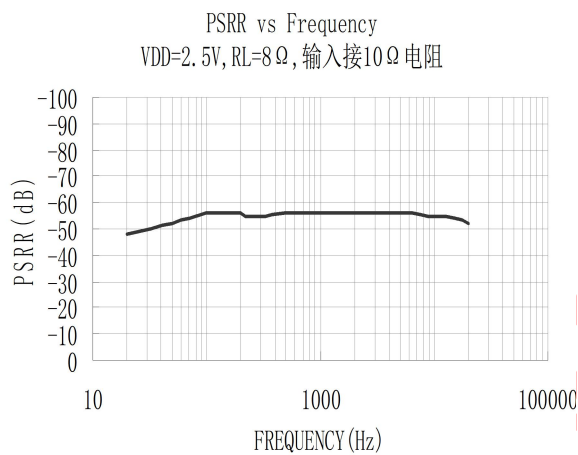
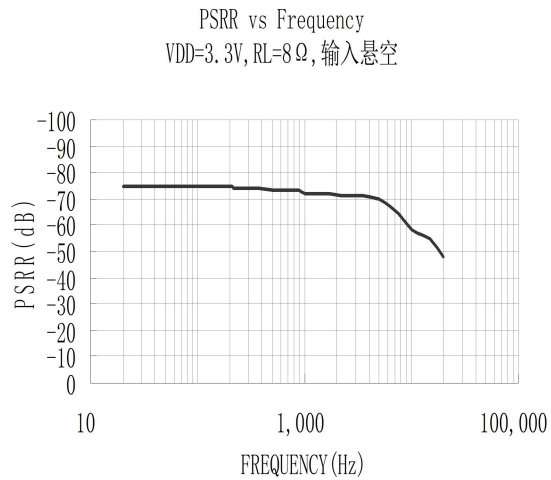
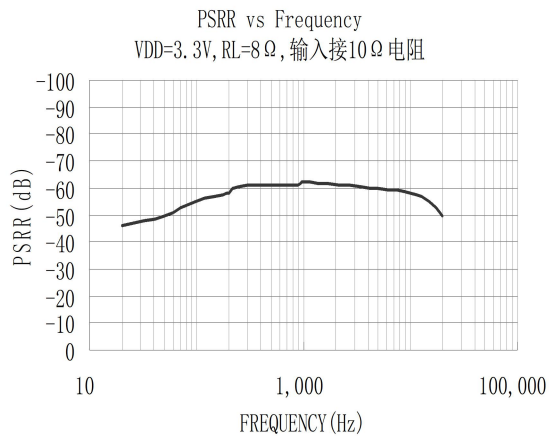
9.2 Supply Voltage Rejection Ratio (PSRR)

PSRR vs Frequency
VDD=5V, RL=8Ω, 输入接10Ω电阻

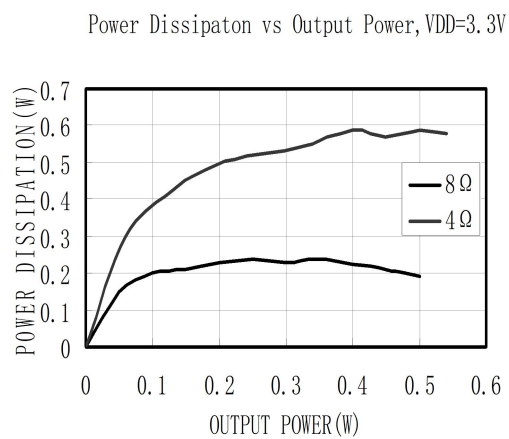
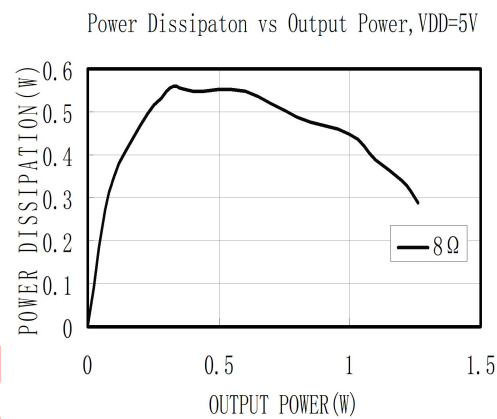


PSRR vs Frequency
VDD=5V, RL=8Ω, 输入悬空

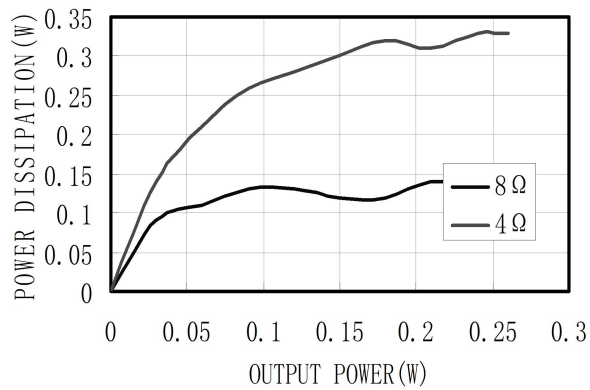




9.3 chip power dissipation (Power Dissipation)

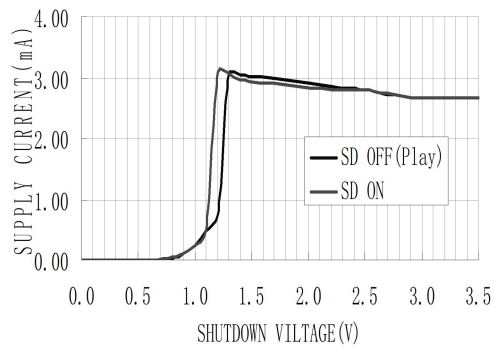


Power Dissipation vs Output Power, VDD=2.5V

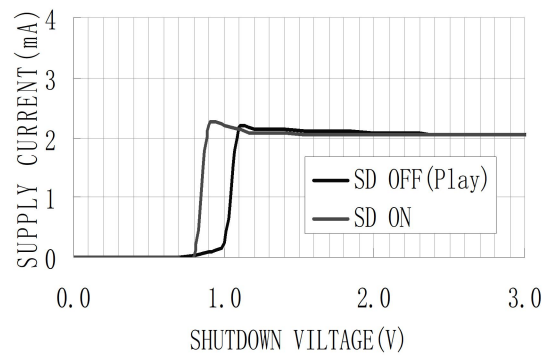


9.4 Shutdown hysteresis (Shut Down Hysteresis)

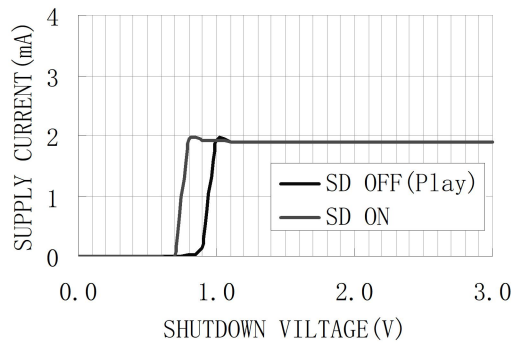
Shutdown Hysteresis Voltage
VDD=5V



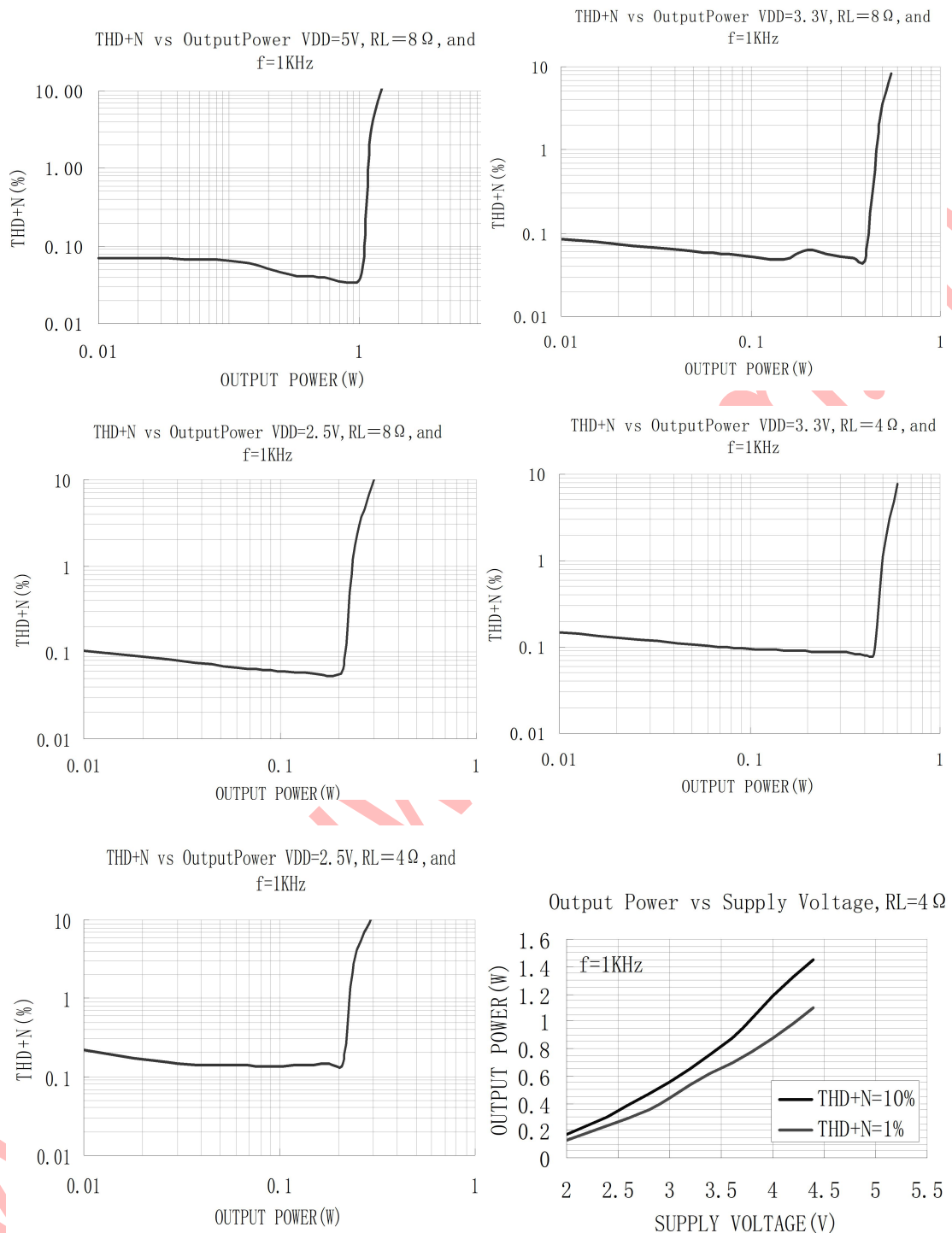
Shutdown Hysteresis Voltage
VDD=3.3V

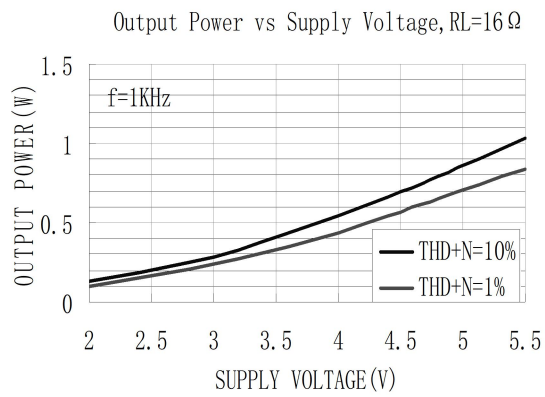
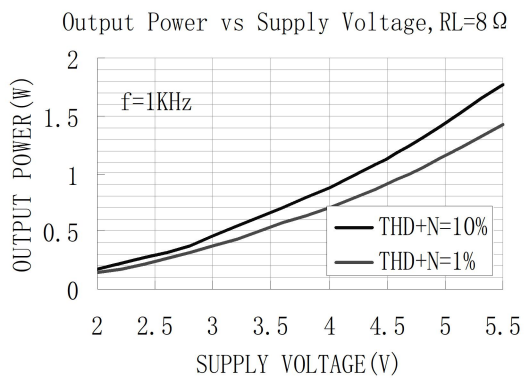


Shutdown Hysteresis Voltage
VDD=2.5V



9.5 Output Power (Output Power)

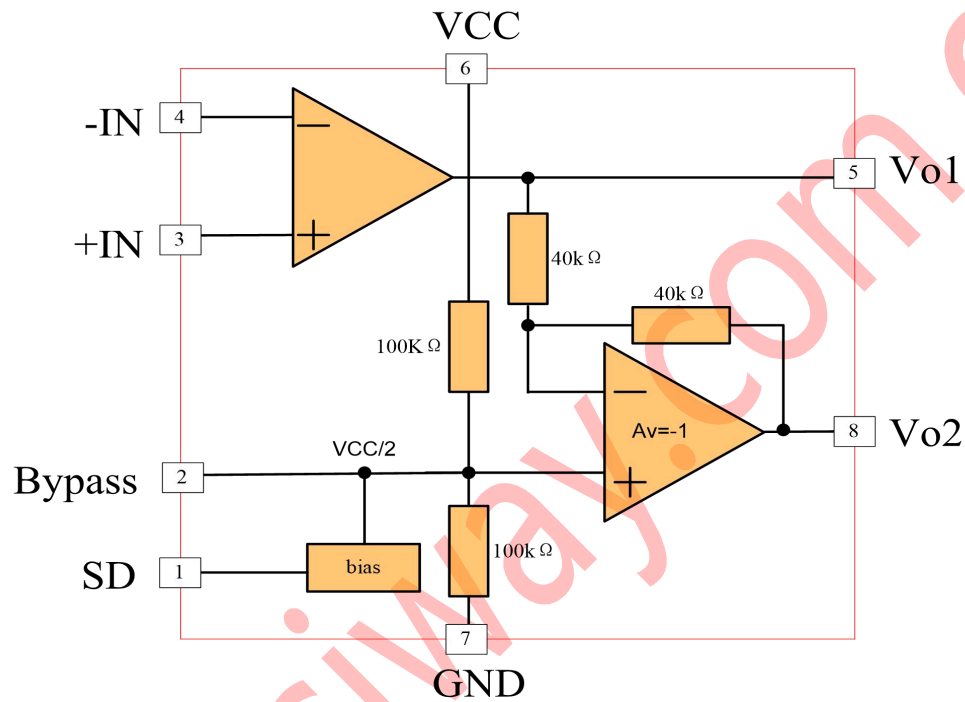




10 Application note

10.1 Chip basic structure description

NS8002It is an audio power amplifier with double-ended output. It integrates two operational amplifiers. The gain of the first amplifier can be set by adjusting the feedback resistor, and the latter is an inverting follower of the voltage, thus forming an amplified drive circuit with a differential output whose gain can be configured. Its principle block diagram is:



10.2 Chip digital logic characteristics

surface1 Shutdown Signal Digital Logic Characteristics

parameter	minimum value	typical value	maximum value	unit	illustrate
The supply voltage is 5V					
VIH		1.5		V	
VIL		1.3		V	
The supply voltage is 3V					
VIH		1.3		V	
VIL		1.0		V	

10.3 External Resistor Configuration

As shown in the application diagram, the gain of the op amp is controlled by an external resistor R_i . R_i decided, its gain is $A_v = 2 \times R_f / R_i$, the chip passes V_{o1} , V_{o2} Output to load, bridge connection.

The bridge connection method has several advantages over single-ended output: First, it saves the external DC blocking filter capacitor. For single-ended output, if the DC blocking capacitor is not connected, there will be a DC voltage at the output terminal, resulting in a DC current output after power-on, which will waste power consumption and easily damage the audio. The second is that the double-ended output is actually a push-pull output. Under the same output voltage, the driving power is increased to single-ended 4 times, the power output is large.

10.4 External Capacitor Configuration

Excessive input capacitance increases cost and area, which is very unfavorable for applications with tight cost and area. Obviously, it is important to determine how much capacitance to use to accomplish the coupling. In fact, in many applications, speakers (Speaker) are not able to reproduce below 100Hz-150Hz low-frequency sounds. Input coupling capacitance C_i (and R_i forming a first-order high-pass) determines the low-frequency response, and the calculation formula is:

$$f_c = \frac{1}{2 \times R_i \times C_i}$$

Therefore, using a large capacitor does not improve the performance of the system. In addition to considering the performance of the system, the suppression performance of switching/switching noise is affected by the capacitance. If the coupling capacitance is large, the delay of the feedback network will be large, resulting in pop noise occurs, so a small coupling capacitor can reduce this noise.

10.5 Chip power consumption

Power consumption is one of the key indicators for the amplifier. The maximum self-power consumption of the differential output amplifier is:

$$P_{dmax} = 4 \times \frac{V_{DD2}}{2 \times R_L}$$

It must be noted that self power dissipation is a function of output power. When designing the circuit, it is not possible to make the junction temperature inside the chip higher than the normal operating temperature. According to the thermal resistance of the chip, to design, you can increase the heat dissipation performance by dissipating copper and platinum yourself. If the chip still does not meet the requirements, you need to increase the load resistance, reduce the power supply voltage or lower the ambient temperature to solve it.

10.6 Power Bypass

In the application of the amplifier, the bypass design of the power supply is very important, especially for the noise performance and power supply voltage suppression performance of the application scheme. In the design, the bypass capacitor should be as close as possible to the chip and the power supply pin. Typical capacitance is 10uF of electrolytic capacitors and 0.1uF of ceramic capacitors.

exist NS8002 application circuit, another capacitor C_b (catch BYP pins) are also very critical, affecting the PSRR, Switching/switching noise performance. general option 0.1uF~1uF of ceramic capacitors.

10.7 power down mode

In order to save power, the amplifier can be turned off when not in use, NS8002 There is a power-down control pin, which can control whether the amplifier works. The level of the control pin must be connected to the control signal that meets the interface requirements, otherwise the chip may enter an indeterminate state and cannot enter the power-down mode, and its self-power consumption is not reduced, and the purpose of power saving cannot be achieved.

11 Version modification history

Disclaimer: Shenzhen Nationway Technology Co., Ltd. reserves the right to modify product information and product specifications at any time without notice. The right to interpret this manual belongs to Shenzhen Nationway Technology Co., Ltd. and is responsible for the final interpretation .

12Package information

